The devices use look-up tables (LUTs) and embedded block memories traditionally associated with FPGAs for flexible and efficient logic implementation. Through non-volatile technology, the devices provide the single-chip, high-security, instant-on capabilities traditionally associated with CPLDs. Finally, advanced process technology and careful design will provide the high pin-to-pin performance also associated with CPLDs.

The ispLEVER® design tools from Lattice allow complex designs to be efficiently implemented using the MachXO family of devices. Popular logic synthesis tools provide synthesis library support for MachXO. The ispLEVER tools use the synthesis tool output along with the constraints from its floor planning tools to place and route the design in the MachXO device. The ispLEVER tool extracts the timing from the routing and back-annotates it into the design for timing verification.

Table 2-8. I/O Support Device by Device

	MachXO256	MachXO640	MachXO1200	MachXO2280
Number of I/O Banks	2	4	8	8
Type of Input Buffers	Single-ended (all I/O Banks)	Single-ended (all I/O Banks)	Single-ended (all I/O Banks) Differential Receivers (all I/O Banks)	Single-ended (all I/O Banks) Differential Receivers (all I/O Banks)
Types of Output Buffers	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks) Differential buffers with true LVDS outputs (50% on left and right side)	Single-ended buffers with complementary outputs (all I/O Banks) Differential buffers with true LVDS outputs (50% on left and right side)
Differential Output Emulation Capability	All I/O Banks	All I/O Banks	All I/O Banks	All I/O Banks
PCI Support	No	No	Top side only	Top side only

Table 2-9. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	**3.3V**	**2.5V**	**1.8V**	**1.5V**	**1.2V**
Single Ended Interfaces					
LVTTL	√	√	√	√	√
LVCMOS33	√	√	√	√	√
LVCMOS25	√	√	√	√	√
LVCMOS18			√		
LVCMOS15				√	
LVCMOS12	√	√	√	√	√
PCI[1]	√				
Differential Interfaces					
BLVDS[2], LVDS[2], LVPECL[2], RSDS[2]	√	√	√	√	√

1. Top Banks of MachXO1200 and MachXO2280 devices only.
2. MachXO1200 and MachXO2280 devices only.

Table 2-10. Supported Output Standards

Output Standard	Drive	V_{CCIO} (Typ.)
Single-ended Interfaces		
LVTTL	4mA, 8mA, 12mA, 16mA	3.3
LVCMOS33	4mA, 8mA, 12mA, 14mA	3.3
LVCMOS25	4mA, 8mA, 12mA, 14mA	2.5
LVCMOS18	4mA, 8mA, 12mA, 14mA	1.8
LVCMOS15	4mA, 8mA	1.5
LVCMOS12	2mA, 6mA	1.2
LVCMOS33, Open Drain	4mA, 8mA, 12mA, 14mA	—
LVCMOS25, Open Drain	4mA, 8mA, 12mA, 14mA	—
LVCMOS18, Open Drain	4mA, 8mA, 12mA, 14mA	—
LVCMOS15, Open Drain	4mA, 8mA	—
LVCMOS12, Open Drain	2mA, 6mA	—
PCI33[3]	N/A	3.3
Differential Interfaces		
LVDS[1, 2]	N/A	2.5
BLVDS, RSDS[2]	N/A	2.5
LVPECL[2]	N/A	3.3

1. MachXO1200 and MachXO2280 devices have dedicated LVDS buffers.
2. These interfaces can be emulated with external resistors in all devices.
3. Top Banks of MachXO1200 and MachXO2280 devices only.

sysIO Buffer Banks

The number of Banks vary between the devices of this family. Eight Banks surround the two larger devices, the MachXO1200 and MachXO2280 (two Banks per side). The MachXO640 has four Banks (one Bank per side). The smallest member of this family, the MachXO256, has only two Banks.

Each sysIO buffer Bank is capable of supporting multiple I/O standards. Each Bank has its own I/O supply voltage (V_{CCIO}) which allows it to be completely independent from the other Banks. Figure 2-18, Figure 2-18, Figure 2-20 and Figure 2-21 shows the sysIO Banks and their associated supplies for all devices.

Absolute Maximum Ratings[1, 2, 3]

	LCMXO E (1.2V)	LCMXO C (1.8V/2.5V/3.3V)
Supply Voltage V_{CC}	-0.5 to 1.32V	-0.5 to 3.75V
Supply Voltage V_{CCAUX}	-0.5 to 3.75V	-0.5 to 3.75V
Output Supply Voltage V_{CCIO}	-0.5 to 3.75V	-0.5 to 3.75V
I/O Tristate Voltage Applied [4]	-0.5 to 3.75V	-0.5 to 3.75V
Dedicated Input Voltage Applied[4]	-0.5 to 3.75V	-0.5 to 4.25V
Storage Temperature (ambient)	-65 to 150°C	-65 to 150°C
Junction Temp. (Tj)	+125°C	+125°C

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice *Thermal Management* document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}	Core Supply Voltage for 1.2V Devices	1.14	1.26	V
	Core Supply Voltage for 1.8V/2.5V/3.3V Devices	1.71	3.465	V
V_{CCAUX}[3]	Auxiliary Supply Voltage	3.135	3.465	V
V_{CCIO}[2]	I/O Driver Supply Voltage	1.14	3.465	V
t_{JCOM}	Junction Temperature Commercial Operation	0	+85	°C
t_{JIND}	Junction Temperature Industrial Operation	-40	100	°C
$t_{JFLASHCOM}$	Junction Temperature, Flash Programming, Commercial	0	+85	°C
$t_{JFLASHIND}$	Junction Temperature, Flash Programming, Industrial	-40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both 2.5V, they must also be the same supply. 3.3V V_{CCIO} and 1.2V V_{CCIO} should be tied to V_{CCAUX} or 1.2V V_{CC} respectively.
2. See recommended voltages by I/O standard in subsequent table.
3. V_{CC} must reach minimum V_{CC} value before V_{CCAUX} reaches 2.5V.

MachXO256 and MachXO640 Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Min.	Typ.	Max	Units
I_{DK}	Input or I/O leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX)	—	—	+/-1000	µA

1. Insensitive to sequence of V_{CC}, V_{CCAUX}, and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC}, V_{CCAUX}, and V_{CCIO}.
2. $0 \le V_{CC} \le V_{CC}$ (MAX), $0 \le V_{CCIO} \le V_{CCIO}$ (MAX) and $0 \le V_{CCAUX} \le V_{CCAUX}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

MachXO1200 and MachXO2280 Hot Socketing Specifications[1, 2, 3, 4]

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
Non-LVDS General Purpose sysIOs						
I_{DK}	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX.)	—	—	+/-1000	µA
LVDS General Purpose sysIOs						
I_{DK_LVDS}	Input or I/O Leakage Current	$V_{IN} \le V_{CCIO}$	—	—	+/-1000	µA
		$V_{IN} > V_{CCIO}$	—	35	—	mA

1. Insensitive to sequence of V_{CC}, V_{CCAUX}, and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC}, V_{CCAUX}, and V_{CCIO}.
2. $0 \le V_{CC} \le V_{CC}$ (MAX), $0 \le V_{CCIO} \le V_{CCIO}$ (MAX), and $0 \le V_{CCAUX} \le V_{CCAUX}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PW} or I_{BH}.
4. LVCMOS and LVTTL only.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4, 5]	Input or I/O Leakage	$0 \le V_{IN} \le (V_{CCIO} - 0.2V)$	—	—	10	µA
		$(V_{CCIO} - 0.2V) < V_{IN} \le 3.6V$	—	—	40	µA
I_{PU}	I/O Active Pull-up Current	$0 \le V_{IN} \le 0.7\ V_{CCIO}$	-30	—	-150	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\le V_{IN} \le V_{IH}$ (MAX)	30	—	150	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	-30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \le V_{IN} \le V_{IH}$ (MAX)	—	—	150	µA
I_{BHHO}	Bus Hold High Overdrive current	$0 \le V_{IN} \le V_{IH}$ (MAX)	—	—	-150	µA
V_{BHT}[3]	Bus Hold trip Points	$0 \le V_{IN} \le V_{IH}$ (MAX)	V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	—	8	—	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	—	8	—	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25°C, f = 1.0MHz
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. Not applicable to SLEEPN pin.
5. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30ns in duration or less with a peak current of 6mA can occur on the high-to-low transition. For MachXO1200 and MachXO2280 true LVDS output pins, V_{IH} must be less than or equal to V_{CCIO}.

Supply Current (Sleep Mode)[1, 2]

Symbol	Parameter	Device	Typ.[3]	Max.	Units
I_{CC}	Core Power Supply	LCMXO256C	12	25	µA
		LCMXO640C	12	25	µA
		LCMXO1200C	12	25	µA
		LCMXO2280C	12	25	µA
I_{CCAUX}	Auxiliary Power Supply	LCMXO256C	1	15	µA
		LCMXO640C	1	25	µA
		LCMXO1200C	1	45	µA
		LCMXO2280C	1	85	µA
I_{CCIO}	Bank Power Supply[4]	All LCMXO 'C' Devices	2	30	µA

1. Assumes all inputs are configured as LVCMOS and held at the VCCIO or GND.
2. Frequency = 0MHz.
3. T_A = 25°C, power supplies at nominal voltage.
4. Per Bank.

Supply Current (Standby)[1, 2, 3, 4]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO256C	7	mA
		LCMXO640C	9	mA
		LCMXO1200C	14	mA
		LCMXO2280C	20	mA
		LCMXO256E	4	mA
		LCMXO640E	6	mA
		LCMXO1200E	10	mA
		LCMXO2280E	12	mA
I_{CCAUX}	Auxiliary Power Supply V_{CCAUX} = 3.3V	LCMXO256E/C	5	mA
		LCMXO640E/C	7	mA
		LCMXO1200E/C	12	mA
		LCMXO2280E/C	13	mA
I_{CCIO}	Bank Power Supply[6]	All devices	2	mA

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND.
3. Frequency = 0MHz.
4. User pattern = blank.
5. T_J = 25ºC, power supplies at nominal voltage.
6. Per Bank. V_{CCIO} = 2.5V. Does not include pull-up/pull-down.

Initialization Supply Current[1, 2, 3, 4]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO256C	13	mA
		LCMXO640C	17	mA
		LCMXO1200C	21	mA
		LCMXO2280C	23	mA
		LCMXO256E	10	mA
		LCMXO640E	14	mA
		LCMXO1200E	18	mA
		LCMXO2280E	20	mA
I_{CCAUX}	Auxiliary Power Supply V_{CCAUX} = 3.3V	LCMXO256E/C	10	mA
		LCMXO640E/C	13	mA
		LCMXO1200E/C	24	mA
		LCMXO2280E/C	25	mA
I_{CCIO}	Bank Power Supply[6]	All devices	2	mA

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.
2. Assumes all I/O pins are held at V_{CCIO} or GND.
3. Frequency = 0MHz.
4. Typical user pattern.
5. T_J = 25°C, power supplies at nominal voltage.
6. Per Bank, V_{CCIO} = 2.5V. Does not include pull-up/pull-down.

Programming and Erase Flash Supply Current[1, 2, 3, 4]

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO256C	9	mA
		LCMXO640C	11	mA
		LCMXO1200C	16	mA
		LCMXO2280C	22	mA
		LCMXO256E	6	mA
		LCMXO640E	8	mA
		LCMXO1200E	12	mA
		LCMXO2280E	14	mA
I_{CCAUX}	Auxiliary Power Supply V_{CCAUX} = 3.3V	LCMXO256C/E	8	mA
		LCMXO640C/E	10	mA
		LCMXO1200/E	15	mA
		LCMXO2280C/E	16	mA
I_{CCIO}	Bank Power Supply[6]	All devices	2	mA

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.
2. Assumes all I/O pins are held at V_{CCIO} or GND.
3. Typical user pattern.
4. JTAG programming is at 25MHz.
5. T_J = 25°C, power supplies at nominal voltage.
6. Per Bank. V_{CCIO} = 2.5V. Does not include pull-up/pull-down.

sysIO Recommended Operating Conditions

Standard	V_{CCIO} (V)		
	Min.	Typ.	Max.
LVCMOS 3.3	3.135	3.3	3.465
LVCMOS 2.5	2.375	2.5	2.625
LVCMOS 1.8	1.71	1.8	1.89
LVCMOS 1.5	1.425	1.5	1.575
LVCMOS 1.2	1.14	1.2	1.26
LVTTL	3.135	3.3	3.465
PCI[3]	3.135	3.3	3.465
LVDS[1, 2]	2.375	2.5	2.625
LVPECL[1]	3.135	3.3	3.465
BLVDS[1]	2.375	2.5	2.625
RSDS[1]	2.375	2.5	2.625

1. Inputs on chip. Outputs are implemented with the addition of external resistors.
2. MachXO1200 and MachXO2280 devices have dedicated LVDS buffers
3. Input on the top bank of the MachXO1200 and MachXO2280 only.

sysIO Single-Ended DC Electrical Characteristics

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL}[1] (mA)	I_{OH}[1] (mA)
	Min. (V)	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3	-0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	16, 12, 8, 4	-14, -12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVTTL	-0.3	0.8	2.0	3.6	0.4	2.4	16	-16
					0.4	V_{CCIO} - 0.4	12, 8, 4	-12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	V_{CCIO} - 0.4	16, 12, 8, 4	-14, -12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS 1.8	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} - 0.4	16, 12, 8, 4	-14, -12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS 1.5	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} - 0.4	8, 4	-8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS 1.2 (“C” Version)	-0.3	0.42	0.78	3.6	0.4	V_{CCIO} - 0.4	6, 2	-6, -2
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS 1.2 (“E” Version)	-0.3	$0.35V_{CC}$	$0.65V_{CC}$	3.6	0.4	V_{CCIO} - 0.4	6, 2	-6, -2
					0.2	V_{CCIO} - 0.2	0.1	-0.1
PCI	-0.3	$0.3V_{CCIO}$	$0.5V_{CCIO}$	3.6	$0.1V_{CCIO}$	$0.9V_{CCIO}$	1.5	-0.5

1. The average DC current drawn by I/Os between GND connections, or between the last GND in an I/O Bank and the end of an I/O Bank, as shown in the logic signal connections table shall not exceed n * 8mA. Where n is the number of I/Os between Bank GND connections or between the last GND in a Bank and the end of a Bank.

MachXO External Switching Characteristics[1]

Over Recommended Operating Conditions

Parameter	Description	Device	-5		-4		-3		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
General I/O Pin Parameters (Using Global Clock without PLL)[1]									
t_{PD}	Best Case t_{PD} Through 1 LUT	LCMXO256	—	3.5	—	4.2	—	4.9	ns
		LCMXO640	—	3.5	—	4.2	—	4.9	ns
		LCMXO1200	—	3.6	—	4.4	—	5.1	ns
		LCMXO2280	—	3.6	—	4.4	—	5.1	ns
t_{CO}	Best Case Clock to Output - From PFU	LCMXO256	—	4.0	—	4.8	—	5.6	ns
		LCMXO640	—	4.0	—	4.8	—	5.7	ns
		LCMXO1200	—	4.3	—	5.2	—	6.1	ns
		LCMXO2280	—	4.3	—	5.2	—	6.1	ns
t_{SU}	Clock to Data Setup - To PFU	LCMXO256	1.3	—	1.6	—	1.8	—	ns
		LCMXO640	1.1	—	1.3	—	1.5	—	ns
		LCMXO1200	1.1	—	1.3	—	1.6	—	ns
		LCMXO2280	1.1	—	1.3	—	1.5	—	ns
t_{H}	Clock to Data Hold - To PFU	LCMXO256	-0.3	—	-0.3	—	-0.3	—	ns
		LCMXO640	-0.1	—	-0.1	—	-0.1	—	ns
		LCMXO1200	0.0	—	0.0	—	0.0	—	ns
		LCMXO2280	-0.4	—	-0.4	—	-0.4	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	LCMXO256	—	600	—	550	—	500	MHz
		LCMXO640	—	600	—	550	—	500	MHz
		LCMXO1200	—	600	—	550	—	500	MHz
		LCMXO2280	—	600	—	550	—	500	MHz
t_{SKEW_PRI}	Global Clock Skew Across Device	LCMXO256	—	200	—	220	—	240	ps
		LCMXO640	—	200	—	220	—	240	ps
		LCMXO1200	—	220	—	240	—	260	ps
		LCMXO2280	—	220	—	240	—	260	ps

1. General timing numbers based on LVCMOS2.5V, 12 mA.

MachXO Internal Timing Parameters[1]

Over Recommended Operating Conditions

Parameter	Description	-5		-4		-3		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
PFU/PFF Logic Mode Timing								
t_{LUT4_PFU}	LUT4 delay (A to D inputs to F output)	—	0.28	—	0.34	—	0.39	ns
t_{LUT6_PFU}	LUT6 delay (A to D inputs to OFX output)	—	0.44	—	0.53	—	0.62	ns
t_{LSR_PFU}	Set/Reset to output of PFU	—	0.90	—	1.08	—	1.26	ns
t_{SUM_PFU}	Clock to Mux (M0,M1) input setup time	0.10	—	0.13	—	0.15	—	ns
t_{HM_PFU}	Clock to Mux (M0,M1) input hold time	-0.05	—	-0.06	—	-0.07	—	ns
t_{SUD_PFU}	Clock to D input setup time	0.13	—	0.16	—	0.18	—	ns
t_{HD_PFU}	Clock to D input hold time	-0.03	—	-0.03	—	-0.04	—	ns
t_{CK2Q_PFU}	Clock to Q delay, D-type register configuration	—	0.40	—	0.48	—	0.56	ns
t_{LE2Q_PFU}	Clock to Q delay latch configuration	—	0.53	—	0.64	—	0.74	ns
t_{LD2Q_PFU}	D to Q throughput delay when latch is enabled	—	0.55	—	0.66	—	0.77	ns
PFU Dual Port Memory Mode Timing								
t_{CORAM_PFU}	Clock to Output	—	0.40	—	0.48	—	0.56	ns
t_{SUDATA_PFU}	Data Setup Time	-0.18	—	-0.22	—	-0.25	—	ns
t_{HDATA_PFU}	Data Hold Time	0.28	—	0.34	—	0.39	—	ns
t_{SUADDR_PFU}	Address Setup Time	-0.46	—	-0.56	—	-0.65	—	ns
t_{HADDR_PFU}	Address Hold Time	0.71	—	0.85	—	0.99	—	ns
t_{SUWREN_PFU}	Write/Read Enable Setup Time	-0.22	—	-0.26	—	-0.30	—	ns
t_{HWREN_PFU}	Write/Read Enable Hold Time	0.33	—	0.40	—	0.47	—	ns
PIO Input/Output Buffer Timing								
t_{IN_PIO}	Input Buffer Delay	—	0.75	—	0.90	—	1.06	ns
t_{OUT_PIO}	Output Buffer Delay	—	1.29	—	1.54	—	1.80	ns
EBR Timing (1200 and 2280 Devices Only)								
t_{CO_EBR}	Clock to output from Address or Data with no output register	—	2.24	—	2.69	—	3.14	ns
t_{COO_EBR}	Clock to output from EBR output Register	—	0.54	—	0.64	—	0.75	ns
t_{SUDATA_EBR}	Setup Data to EBR Memory	-0.26	—	-0.31	—	-0.37	—	ns
t_{HDATA_EBR}	Hold Data to EBR Memory	0.41	—	0.49	—	0.57	—	ns
t_{SUADDR_EBR}	Setup Address to EBR Memory	-0.26	—	-0.31	—	-0.37	—	ns
t_{HADDR_EBR}	Hold Address to EBR Memory	0.41	—	0.49	—	0.57	—	ns
t_{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory	-0.17	—	-0.20	—	-0.23	—	ns
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.26	—	0.31	—	0.36	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.19	—	0.23	—	0.27	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	-0.13	—	-0.16	—	-0.18	—	ns
t_{RSTO_EBR}	Reset To Output Delay Time from EBR Output Register	—	1.03	—	1.23	—	1.44	ns
PLL Parameters (1200 and 2280 Devices Only)								
t_{RSTREC}	Reset Recovery to Rising Clock	1.00	—	1.00	—	1.00	—	ns
t_{RSTSU}	Reset Signal Setup Time	1.00	—	1.00	—	1.00	—	ns

1. Internal parameters are characterized but not tested on every device.

MachXO Family Timing Adders[1, 2, 3]

Over Recommended Operating Conditions

Buffer Type	Description	-5	-4	-3	Units
Input Adjusters					
LVDS25[4]	LVDS	0.44	0.53	0.61	ns
BLVDS25[4]	BLVDS	0.44	0.53	0.61	ns
LVPECL33[4]	LVPECL	0.42	0.50	0.59	ns
LVTTL33	LVTTL	0.01	0.01	0.01	ns
LVCMOS33	LVCMOS 3.3	0.01	0.01	0.01	ns
LVCMOS25	LVCMOS 2.5	0.00	0.00	0.00	ns
LVCMOS18	LVCMOS 1.8	0.07	0.08	0.10	ns
LVCMOS15	LVCMOS 1.5	0.14	0.17	0.19	ns
LVCMOS12	LVCMOS 1.2	0.40	0.48	0.56	ns
PCI33[4]	PCI	0.01	0.01	0.01	ns
Output Adjusters					
LVDS25E	LVDS 2.5 E	-0.13	-0.15	-0.18	ns
LVDS25[4]	LVDS 2.5	-0.21	-0.26	-0.30	ns
BLVDS25	BLVDS 2.5	-0.03	-0.03	-0.04	ns
LVPECL33	LVPECL 3.3	0.04	0.04	0.05	ns
LVTTL33_4mA	LVTTL 4mA drive	0.04	0.04	0.05	ns
LVTTL33_8mA	LVTTL 8mA drive	0.06	0.07	0.08	ns
LVTTL33_12mA	LVTTL 12mA drive	-0.01	-0.01	-0.01	ns
LVTTL33_16mA	LVTTL 16mA drive	0.50	0.60	0.70	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive	0.04	0.04	0.05	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive	0.06	0.07	0.08	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive	-0.01	-0.01	-0.01	ns
LVCMOS33_14mA	LVCMOS 3.3 14mA drive	0.50	0.60	0.70	ns
LVCMOS25_4mA	LVCMOS 2.5 4mA drive	0.05	0.06	0.07	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive	0.10	0.12	0.13	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive	0.00	0.00	0.00	ns
LVCMOS25_14mA	LVCMOS 2.5 14mA drive	0.34	0.40	0.47	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive	0.11	0.13	0.15	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive	0.05	0.06	0.06	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive	-0.06	-0.07	-0.08	ns
LVCMOS18_14mA	LVCMOS 1.8 14mA drive	0.06	0.07	0.09	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive	0.15	0.19	0.22	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive	0.05	0.06	0.07	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive	0.26	0.31	0.36	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive	0.05	0.06	0.07	ns
PCI33[4]	PCI33	1.85	2.22	2.59	ns

1. Timing adders are characterized but not tested on every device.
2. LVCMOS timing is measured with the load specified in Switching Test Conditions table.
3. All other standards tested according to the appropriate specifications.
4. I/O standard only available in LCMXO1200 and LCMXO2280 devices.

sysCLOCK PLL Timing

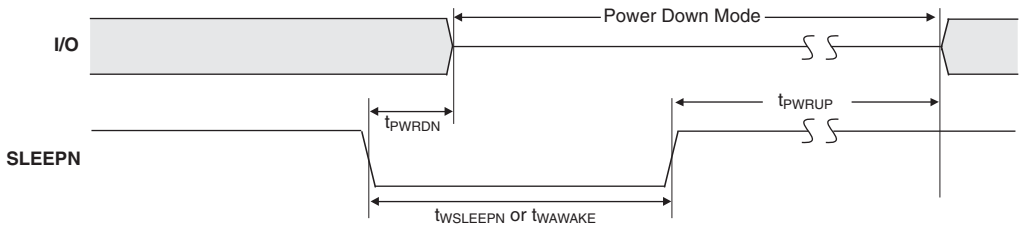
Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		25	420	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)		25	420	MHz
f_{OUT2}	K-Divider Output Frequency (CLKOK)		0.195	210	MHz
f_{VCO}	PLL VCO Frequency		420	840	MHz
f_{PFD}	Phase Detector Input Frequency		25	—	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	Default duty cycle selected[3]	45	55	%
t_{PH}[4]	Output Phase Accuracy		—	0.05	UI
t_{OPJIT}[1]	Output Clock Period Jitter	Fout ≥ 100MHz	—	+/-120	ps
		Fout < 100MHz	—	0.02	UIPP
t_{SK}	Input Clock to Output Clock Skew	Divider ratio = integer	—	+/-200	ps
t_W	Output Clock Pulse Width	At 90% or 10%[3]	1	—	ns
t_{LOCK}[2]	PLL Lock-in Time		—	150	µs
t_{PA}	Programmable Delay Unit		100	450	ps
t_{IPJIT}	Input Clock Period Jitter		—	+/-200	ps
t_{FBKDLY}	External Feedback Delay		—	10	ns
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{RST}	RST Pulse Width		10	—	ns

1. Jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. CLKOS as compared to CLKOP output.

MachXO "C" Sleep Mode Timing

Symbol	Parameter	Device	Min.	Typ.	Max	Units
t_{PWRDN}	SLEEPN Low to Power Down	All	—	—	400	ns
t_{PWRUP}	SLEEPN High to Power Up	LCMXO256	—	—	400	µs
		LCMXO640	—	—	600	µs
		LCMXO1200	—	—	800	µs
		LCMXO2280	—	—	1000	µs
$t_{WSLEEPN}$	SLEEPN Pulse Width	All	400	—	—	ns
t_{WAWAKE}	SLEEPN Pulse Rejection	All	—	—	100	ns



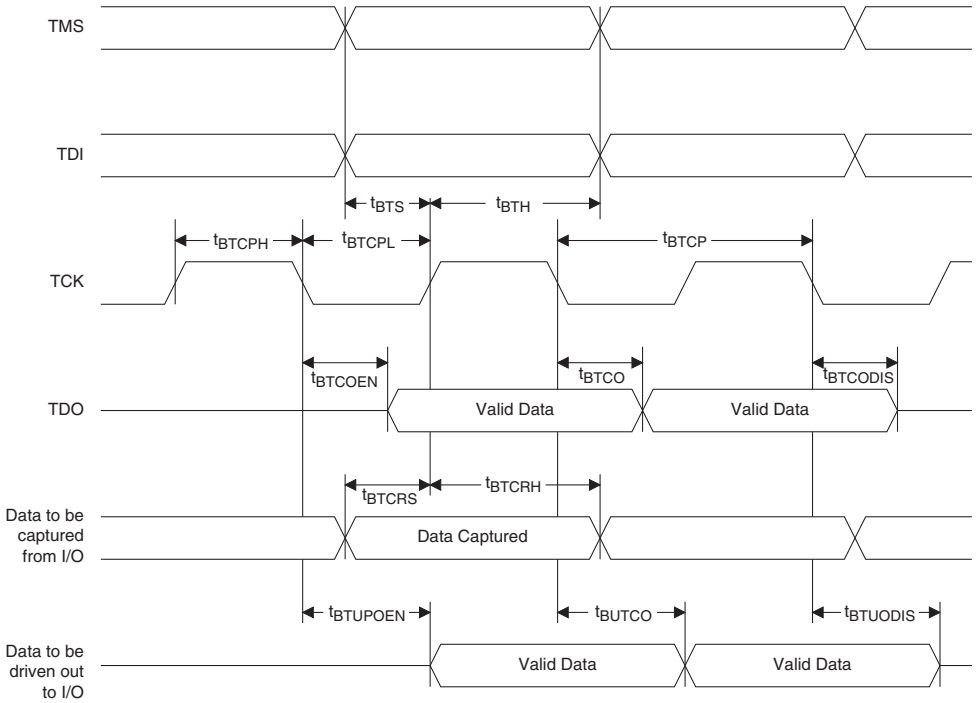
Flash Download Time

Symbol	Parameter		Min.	Typ.	Max.	Units
$t_{REFRESH}$	Minimum V_{CC} or V_{CCAUX} (later of the two supplies) to Device I/O Active	LCMXO256	—	—	0.4	ms
		LCMXO640	—	—	0.6	ms
		LCMXO1200	—	—	0.8	ms
		LCMXO2280	—	—	1.0	ms

JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	TCK [BSCAN] clock frequency	—	25	MHz
t_{BTCP}	TCK [BSCAN] clock pulse width	40	—	ns
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	8	—	ns
t_{BTH}	TCK [BSCAN] hold time	10	—	ns
t_{BTRF}	TCK [BSCAN] rise/fall time	50	—	mV/ns
t_{BTCO}	TAP controller falling edge of clock to output valid	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to output disabled	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to output enabled	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	25	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to output valid	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to output disabled	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to output enabled	—	25	ns

Figure 3-5. JTAG Port Timing Waveforms



MachXO Family Data Sheet Ordering Information

Part Number Description

LCMXO XXXX X – X XXXXXX X XX

Device Family
MachXO PLD

Logic Capacity
256 LUTs = 256
640 LUTs = 640
1200 LUTs = 1200
2280 LUTs = 2280

Supply Voltage
C = 1.8V/2.5V/3.3V
E = 1.2V

Note: Parts dual marked as described.

Speed
3 = Slowest
4
5 = Fastest

Package
T100 = 100-pin TQFP
T144 = 144-pin TQFP
M100 = 100-ball csBGA
M132 = 132-ball csBGA
FT256 = 256-ball ftBGA
FT324 = 324-ball ftBGA

TN100 = 100-pin Lead-Free TQFP
TN144 = 144-pin Lead-Free TQFP
MN100 = 100-ball Lead-Free csBGA
MN132 = 132-ball Lead-Free csBGA
FTN256 = 256-ball Lead-Free ftBGA
FTN324 = 324-ball Lead-Free ftBGA

Grade
C = Commercial
I = Industrial

ES = Engineering Sample
Blank = Production Device

Ordering Information

Note: MachXO devices are dual marked except the slowest commercial speed grade device. For example the commercial speed grade LCMXO640E-4F256C is also marked with industrial grade -3I grade. The slowest commercial speed grade does not have industrial markings. The markings appears as follows:

Dual Mark

All other br

Lead-Free Packaging

Industrial

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO256C-3TN100I	256	1.8V/2.5V/3.3V	78	-3	Lead-Free TQFP	100	IND
LCMXO256C-4TN100I	256	1.8V/2.5V/3.3V	78	-4	Lead-Free TQFP	100	IND
LCMXO256C-3MN100I	256	1.8V/2.5V/3.3V	78	-3	Lead-Free csBGA	100	IND
LCMXO256C-4MN100I	256	1.8V/2.5V/3.3V	78	-4	Lead-Free csBGA	100	IND

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO640C-3TN100I	640	1.8V/2.5V/3.3V	74	-3	Lead-Free TQFP	100	IND
LCMXO640C-4TN100I	640	1.8V/2.5V/3.3V	74	-4	Lead-Free TQFP	100	IND
LCMXO640C-3MN100I	640	1.8V/2.5V/3.3V	74	-3	Lead-Free csBGA	100	IND
LCMXO640C-4MN100I	640	1.8V/2.5V/3.3V	74	-4	Lead-Free csBGA	100	IND
LCMXO640C-3TN144I	640	1.8V/2.5V/3.3V	113	-3	Lead-Free TQFP	144	IND
LCMXO640C-4TN144I	640	1.8V/2.5V/3.3V	113	-4	Lead-Free TQFP	144	IND
LCMXO640C-3MN132I	640	1.8V/2.5V/3.3V	101	-3	Lead-Free csBGA	132	IND
LCMXO640C-4MN132I	640	1.8V/2.5V/3.3V	101	-4	Lead-Free csBGA	132	IND
LCMXO640C-3FTN256I	640	1.8V/2.5V/3.3V	159	-3	Lead-Free ftBGA	256	IND
LCMXO640C-4FTN256I	640	1.8V/2.5V/3.3V	159	-4	Lead-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO1200C-3TN100I	1200	1.8V/2.5V/3.3V	73	-3	Lead-Free TQFP	100	IND
LCMXO1200C-4TN100I	1200	1.8V/2.5V/3.3V	73	-4	Lead-Free TQFP	100	IND
LCMXO1200C-3TN144I	1200	1.8V/2.5V/3.3V	113	-3	Lead-Free TQFP	144	IND
LCMXO1200C-4TN144I	1200	1.8V/2.5V/3.3V	113	-4	Lead-Free TQFP	144	IND
LCMXO1200C-3MN132I	1200	1.8V/2.5V/3.3V	101	-3	Lead-Free csBGA	132	IND
LCMXO1200C-4MN132I	1200	1.8V/2.5V/3.3V	101	-4	Lead-Free csBGA	132	IND
LCMXO1200C-3FTN256I	1200	1.8V/2.5V/3.3V	211	-3	Lead-Free ftBGA	256	IND
LCMXO1200C-4FTN256I	1200	1.8V/2.5V/3.3V	211	-4	Lead-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO2280C-3TN100I	2280	1.8V/2.5V/3.3V	73	-3	Lead-Free TQFP	100	IND
LCMXO2280C-4TN100I	2280	1.8V/2.5V/3.3V	73	-4	Lead-Free TQFP	100	IND
LCMXO2280C-3TN144I	2280	1.8V/2.5V/3.3V	113	-3	Lead-Free TQFP	144	IND
LCMXO2280C-4TN144I	2280	1.8V/2.5V/3.3V	113	-4	Lead-Free TQFP	144	IND
LCMXO2280C-3MN132I	2280	1.8V/2.5V/3.3V	101	-3	Lead-Free csBGA	132	IND
LCMXO2280C-4MN132I	2280	1.8V/2.5V/3.3V	101	-4	Lead-Free csBGA	132	IND
LCMXO2280C-3FTN256I	2280	1.8V/2.5V/3.3V	211	-3	Lead-Free ftBGA	256	IND
LCMXO2280C-4FTN256I	2280	1.8V/2.5V/3.3V	211	-4	Lead-Free ftBGA	256	IND
LCMXO2280C-3FTN324I	2280	1.8V/2.5V/3.3V	271	-3	Lead-Free ftBGA	324	IND
LCMXO2280C-4FTN324I	2280	1.8V/2.5V/3.3V	271	-4	Lead-Free ftBGA	324	IND